

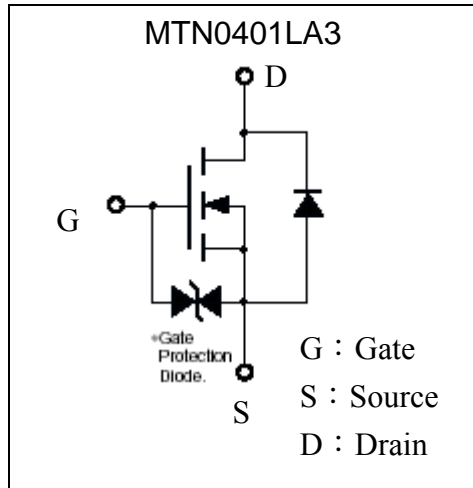
**N-Channel MOSFET**

# MTN0401LA3

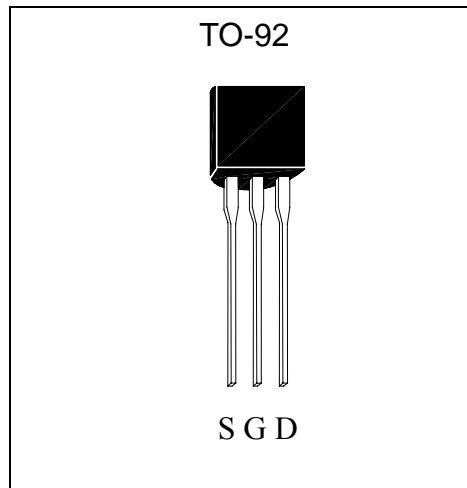
**Features**

- Low on-resistance
- High ESD
- High speed switching
- Low-voltage drive(4V)
- Easily designed drive circuits
- Easy to use in parallel
- Pb-free lead plating and halogen-free package

**Symbol**

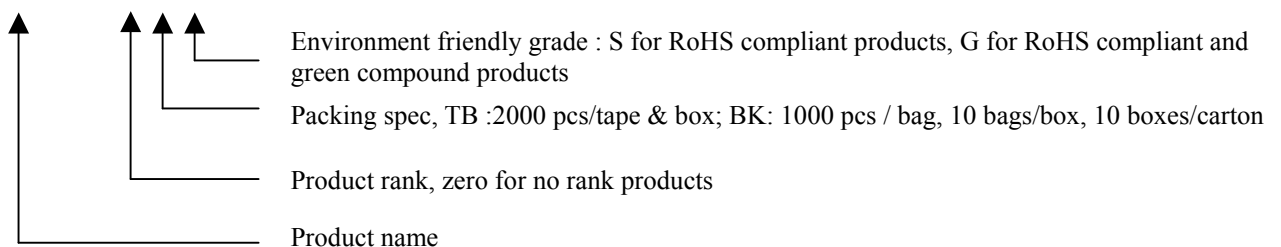


**Outline**



**Ordering Information**

Device	Package	Shipping
MTN0401LA3-0-TB-G	TO-92 (Pb-free lead plating and halogen-freepackage)	2000 pcs / Tape & Box
MTN0401LA3-0-BK-G	TO-92 (Pb-free lead plating and halogen-free package)	1000 pcs/ bag, 10 bags/box, 10boxes/carton





**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Ta=25°C)	I <sub>D</sub>	640	mA
Continuous Drain Current (Ta=100°C)	I <sub>D</sub>	380	mA
Pulsed Drain Current (Ta=25°C)	I <sub>DM</sub>	3 (Note 1)	A
ESD susceptibility		2000 (Note 2)	V
Total Power Dissipation (Ta=25°C) Derate above 25 °C	P <sub>D</sub>	800 3.2	mW mW/°C
Operating Junction Temperature	T <sub>J</sub>	-55~+150	°C
Storage Temperature	T <sub>stg</sub>	-55~+150	°C
Thermal Resistance, Junction to Ambient	R <sub>th,JA</sub>	156	°C/W
Lead Temperature, for 10 second soldering	T <sub>L</sub>	260	°C

Note : \*1. Pulse Width ≤ 300μs, Duty cycle ≤ 2%  
 \*2. Human body model, 1.5kΩ in series with 100pF

**Electrical Characteristics (Ta=25°C)**

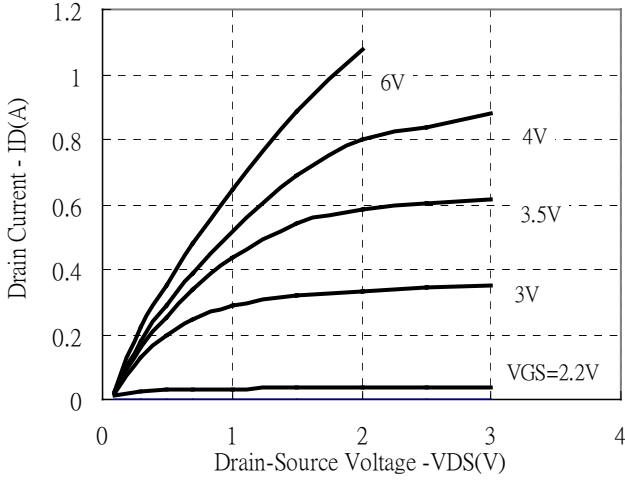
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>DSS</sub>	60	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =10μA
V <sub>GS(th)</sub>	0.5	-	2.5	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =0.25mA
I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =48V, V <sub>GS</sub> =0
*I <sub>D(ON)</sub>	250	-	-	mA	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V
*I <sub>D(ON)</sub>	640	-	-	mA	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V
*R <sub>DS(ON)</sub>	-	-	5	Ω	I <sub>D</sub> =50mA, V <sub>GS</sub> =3.5V
	-	-	5		I <sub>D</sub> =75mA, V <sub>GS</sub> =4.5V
	-	-	3		I <sub>D</sub> =1A, V <sub>GS</sub> =10V
*G <sub>FS</sub>	150	-	-	mS	V <sub>DS</sub> =10V, I <sub>D</sub> =200mA
C <sub>iss</sub>	-	-	60	pF	V <sub>DS</sub> =15V, V <sub>GS</sub> =0, f=1MHz
C <sub>oss</sub>	-	-	50		
C <sub>rss</sub>	-	-	15		

\*Pulse Test : Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

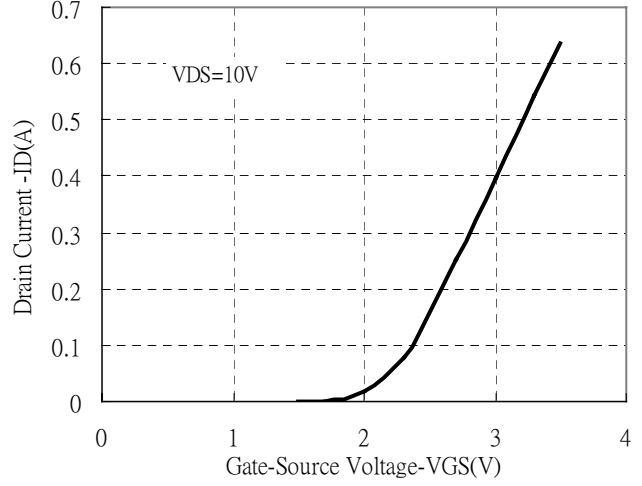


### Typical Characteristics

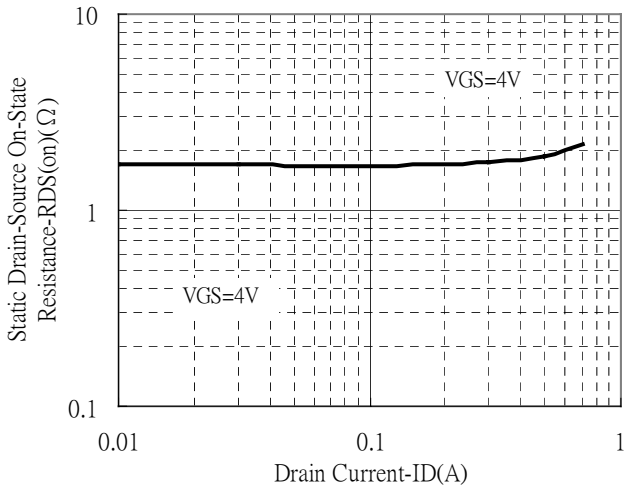
Typical Output Characteristics



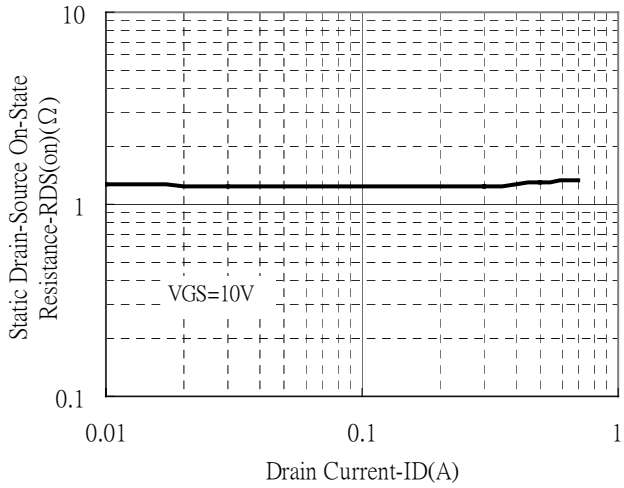
Typical Transfer Characteristics



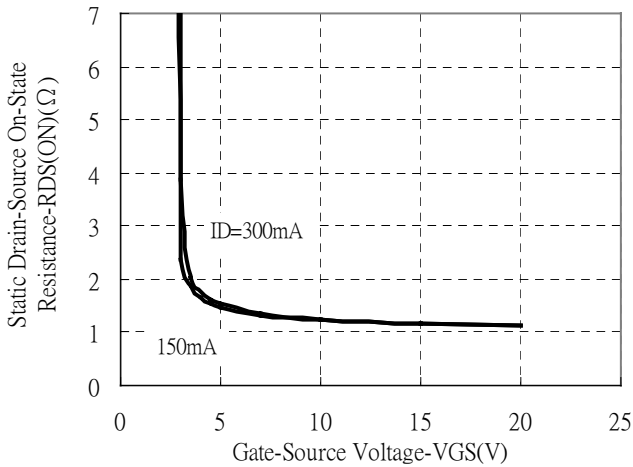
Static Drain-Source On-State resistance vs Drain Current



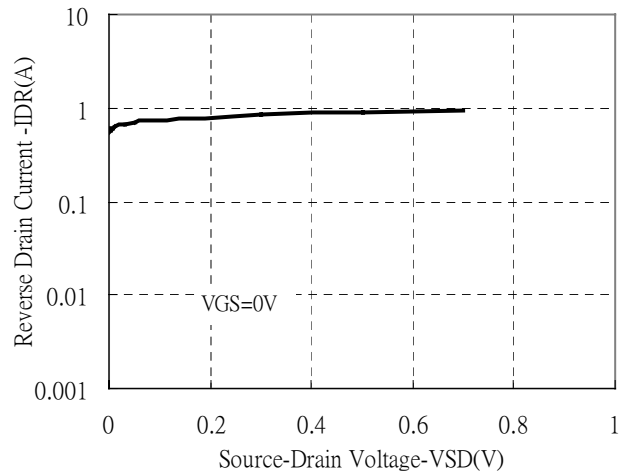
Static Drain-Source On-State resistance vs Drain Current



Static Drain-Source On-State Resistance vs Gate-Source Voltage



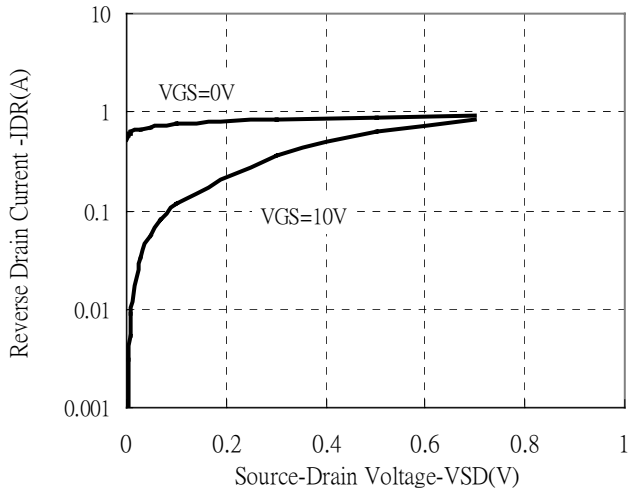
Reverse Drain Current vs Source-Drain Voltage



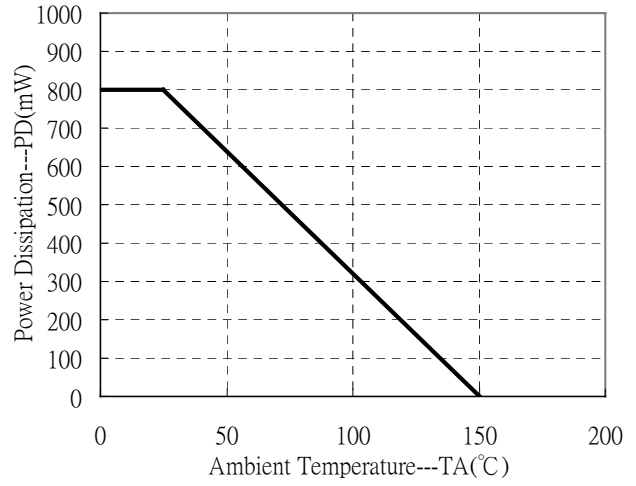


### Typical Characteristics(Cont.)

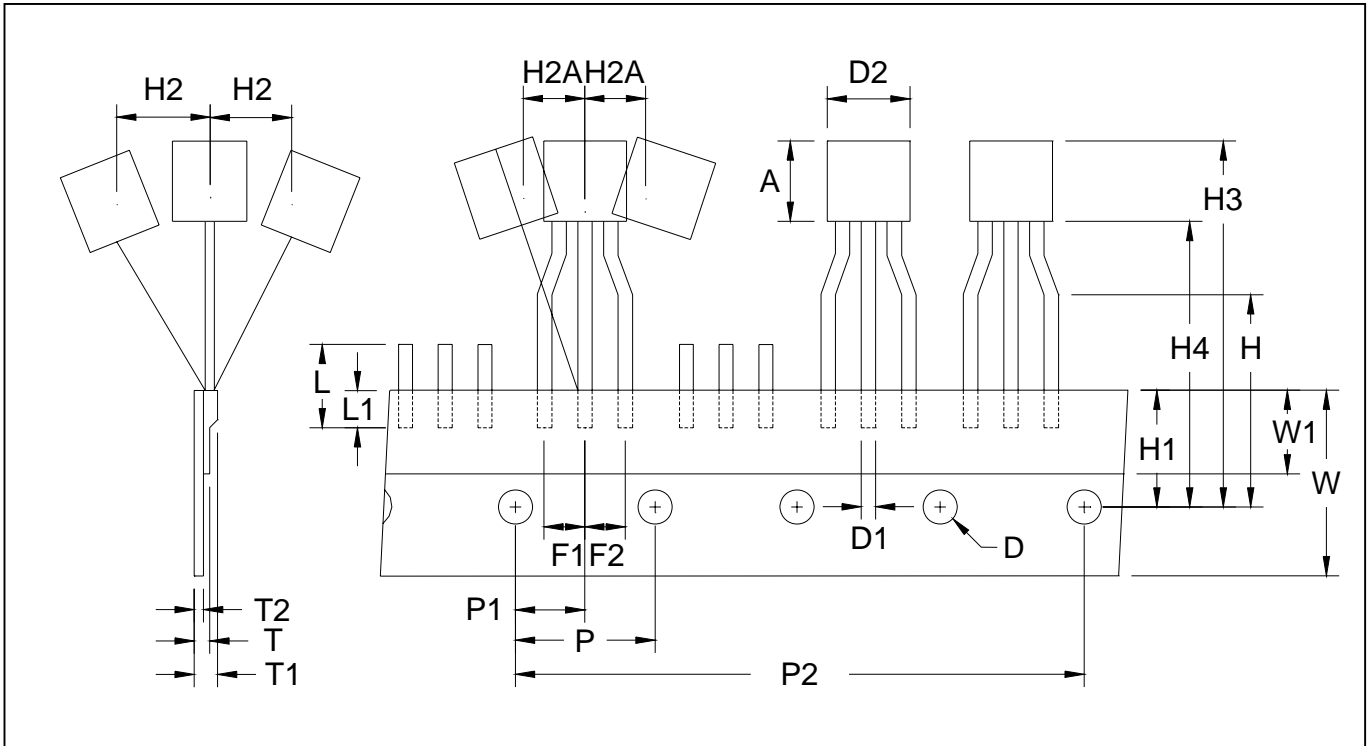
Reverse Drain Current vs Source-Drain Voltage



Power Derating Curve

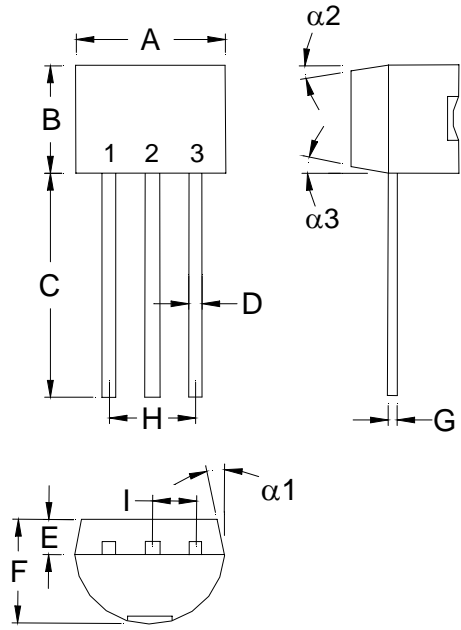


**TO-92 Taping Outline**



DIM	Item	Millimeters	
		Min.	Max.
A	Component body height	4.33	4.83
D	Tape Feed Diameter	3.80	4.20
D1	Lead Diameter	0.36	0.53
D2	Component Body Diameter	4.33	4.83
F1,F2	Component Lead Pitch	2.40	2.90
F1,F2	F1-F2	-	±0.3
H	Height Of Seating Plane	15.50	16.50
H1	Feed Hole Location	8.50	9.50
H2	Front To Rear Deflection	-	1
H2A	Deflection Left Or Right	-	1
H3	Component Height	-	27
H4	Feed Hole To Bottom Of Component	-	21
L	Lead Length After Component Removal	-	11
L1	Lead Wire Enclosure	2.50	-
P	Feed Hole Pitch	12.50	12.90
P1	Center Of Seating Plane Location	5.95	6.75
P2	4 Feed Hole Pitch	50.30	51.30
T	Over All Tape Thickness	-	0.55
T1	Total Taped Package Thickness	-	1.42
T2	Carrier Tape Thickness	0.36	0.68
W	Tape Width	17.50	19.00
W1	Adhesive Tape Width	5.00	7.00
-	20 pcs Pitch	253	255

**TO-92 Dimension**



Marking:

TN  
0401L  
F0330A

Style: Pin 1.Source 2.Gate 3.Drain

3-Lead TO-92 Plastic Package  
CYStek Package Code: A3

\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°

Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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